

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI ULBM2TE is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.40 A
V_{CB0}	36 V
V_{CEO}	16 V
V_{EBO}	4.0 V
P_{DISS}	5 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	35 °C/W

PACKAGE STYLE TO-39GE

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.200 / 5.080	
B	.029 / 0.740	.045 / 1.140
C	.028 / 0.720	.034 / 0.860
D	.355 / 9.020	.370 / 9.370
E	.315 / 8.010	.335 / 8.500
F	.165 / 4.200	.180 / 4.570
G	.500 / 12.700	.750 / 19.050
H	.016 / 0.410	.020 / 0.508

ORDER CODE: ASI10679

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	16			V
BV_{CES}	I _C = 50 mA R _{BE} = 10 Ω	36			V
BV_{EBO}	I _E = 1.0 mA	4.0			V
I_{CB0}	V _{CB} = 15 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 50 mA	20		200	---
C_{ob}	V _{CB} = 12.5 V f = 1.0 MHz			10	pF
P_G	V _{CE} = 12.5 V P _{OUT} = 2.0 W f = 470 MHz	8.0			dB
η_c			55		%